



**AO4614**

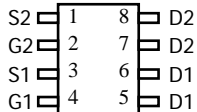
**Complementary Enhancement Mode Field Effect Transistor**

**General Description**

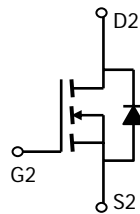
The AO4614 uses advanced trench technology MOSFETs to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs may be used in H-bridge, Inverters and other applications. *Standard Product AO4614 is Pb-free (meets ROHS & Sony 259 specifications). AO4614L is a Green Product ordering option. AO4614 and AO4614L are electrically identical.*

**Features**

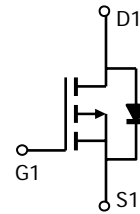
n-channel	p-channel
$V_{DS} (V) = 40V$	-40V
$I_D = 6A (V_{GS}=10V)$	-5A ( $V_{GS} = -10V$ )
$R_{DS(ON)}$	$R_{DS(ON)}$
< 31m $\Omega$ ( $V_{GS}=10V$ )	< 45m $\Omega$ ( $V_{GS} = -10V$ )
< 45m $\Omega$ ( $V_{GS}=4.5V$ )	< 63m $\Omega$ ( $V_{GS} = -4.5V$ )



**SOIC-8**



**n-channel**



**p-channel**

**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	$V_{DS}$	40	-40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ C$	6	-5
		$T_A=70^\circ C$	5	-4
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	20	-20	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	2	2
		$T_A=70^\circ C$	1.28	1.28
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ C$

**Thermal Characteristics: n-channel and p-channel**

Parameter	Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	n-ch	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		n-ch	74	110	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	n-ch	35	50	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	p-ch	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		p-ch	74	110	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	p-ch	35	50	$^\circ C/W$

N Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=10\text{mA}, V_{GS}=0\text{V}$	40			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=32\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1	$\mu\text{A}$
					5	
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	2.3	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}, V_{DS}=5\text{V}$	20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=6\text{A}$ $T_J=125^\circ\text{C}$		23.2	31	m $\Omega$
				36	48	
		$V_{GS}=4.5\text{V}, I_D=5\text{A}$		32.6	45	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}, I_D=6\text{A}$		22		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.77	1	V
$I_S$	Maximum Body-Diode Continuous Current				3	A
<b>DYNAMIC PARAMETERS</b>						
$C_{ISS}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=20\text{V}, f=1\text{MHz}$		404		pF
$C_{OSS}$	Output Capacitance			95		pF
$C_{RSS}$	Reverse Transfer Capacitance			37		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		2.7		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=20\text{V}, I_D=6\text{A}$		8.3		nC
$Q_g(4.5\text{V})$	Total Gate Charge			4.2		nC
$Q_{gs}$	Gate Source Charge			1.3		nC
$Q_{gd}$	Gate Drain Charge			2.3		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}, V_{DS}=20\text{V}, R_L=3.3\Omega,$ $R_{GEN}=3\Omega$		4.2		ns
$t_r$	Turn-On Rise Time			3.3		ns
$t_{D(off)}$	Turn-Off DelayTime			15.6		ns
$t_f$	Turn-Off Fall Time			3		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		20.5		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		14.5		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t_s \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CANNEL

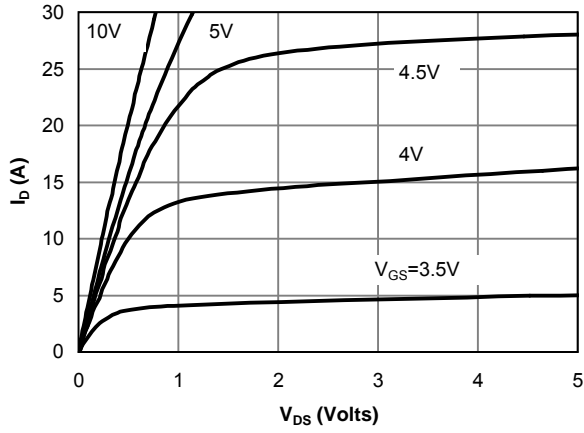


Fig 1: On-Region Characteristics

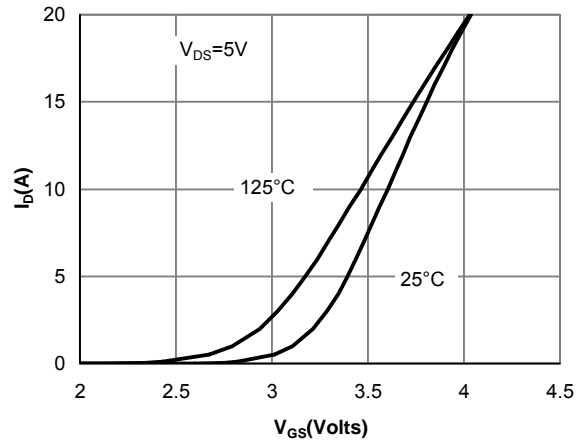


Figure 2: Transfer Characteristics

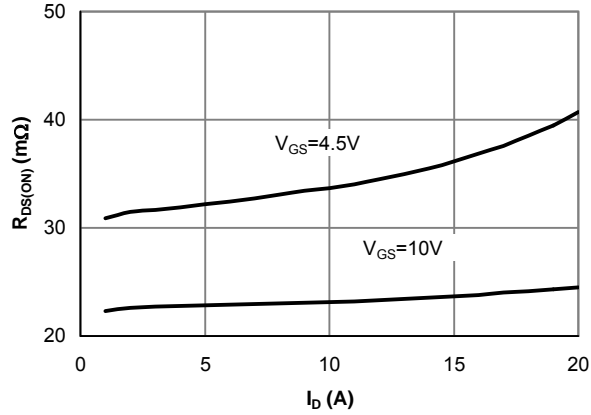


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

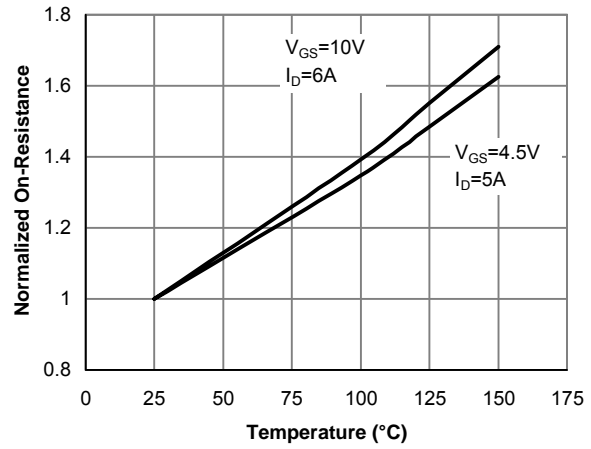


Figure 4: On-Resistance vs. Junction Temperature

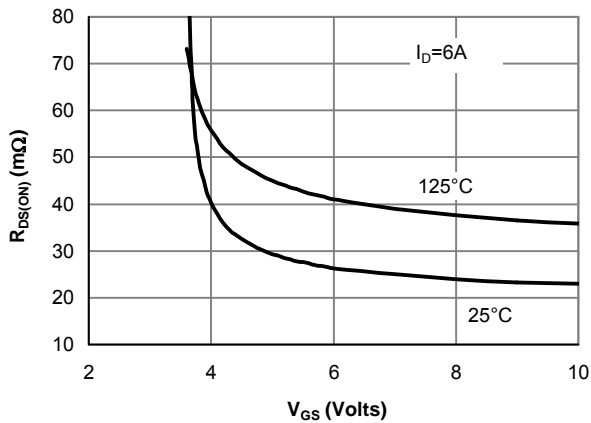


Figure 5: On-Resistance vs. Gate-Source Voltage

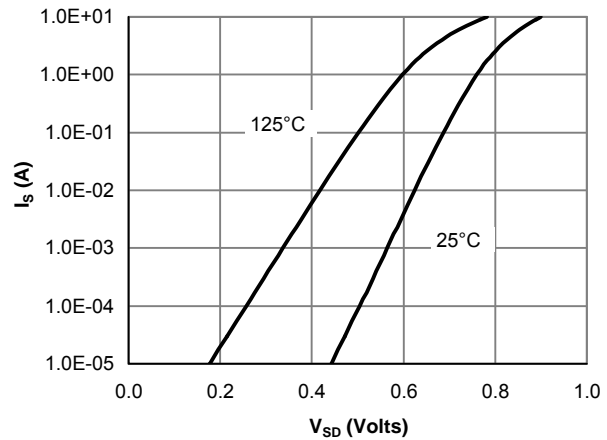


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CANNEL

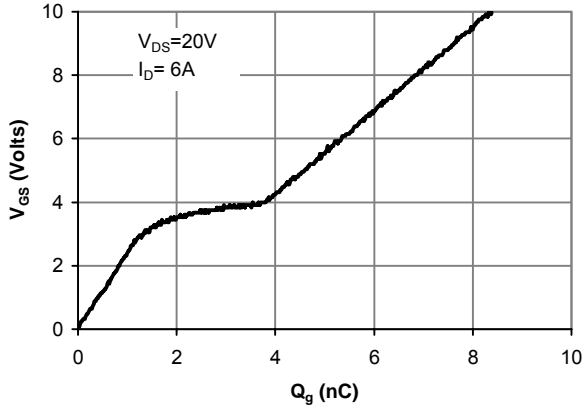


Figure 7: Gate-Charge Characteristics

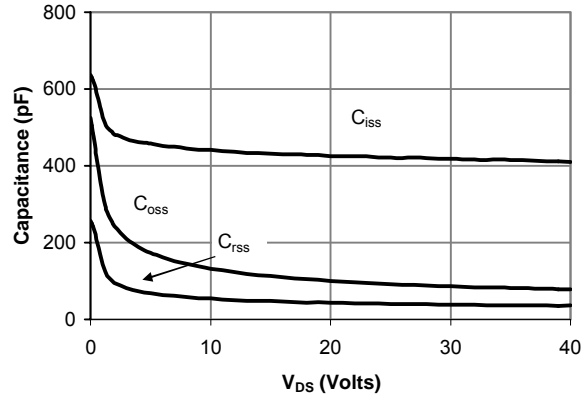


Figure 8: Capacitance Characteristics

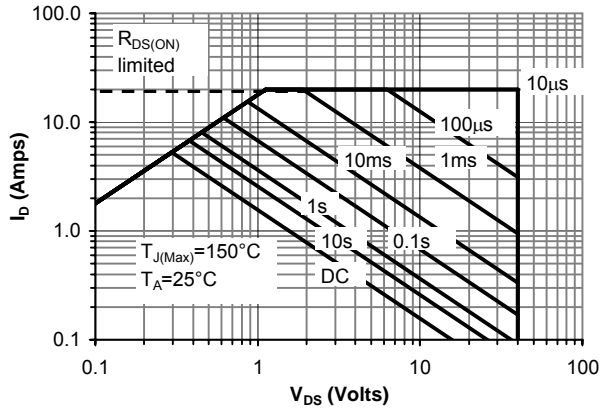


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

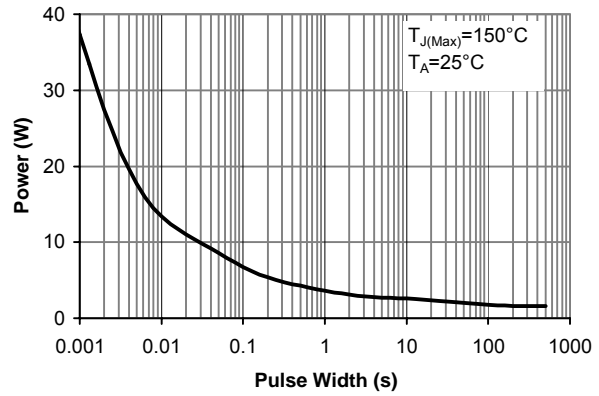


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

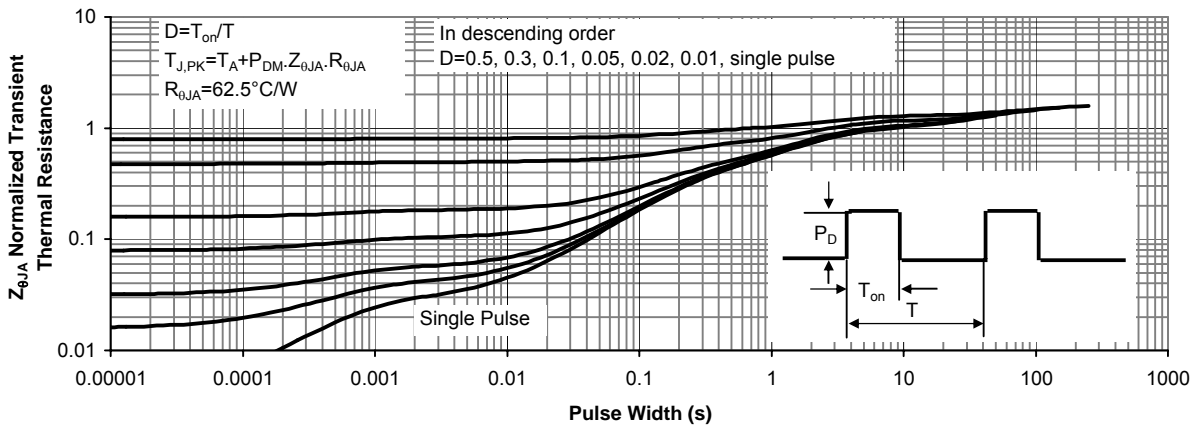


Figure 11: Normalized Maximum Transient Thermal Impedance

P-Channel Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-10\text{mA}$ , $V_{GS}=0\text{V}$	-40			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-32\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1	$\mu\text{A}$
					-5	
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=-250\mu\text{A}$	-1	-1.9	-3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$ , $V_{DS}=-5\text{V}$	-20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$ , $I_D=-5\text{A}$ $T_J=125^\circ\text{C}$		34.7	45	m $\Omega$
				52	65	
		$V_{GS}=-4.5\text{V}$ , $I_D=-2\text{A}$		50.6	63	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}$ , $I_D=-4.8\text{A}$		12		S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}$ , $V_{GS}=0\text{V}$		-0.75	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-3.2	A
<b>DYNAMIC PARAMETERS</b>						
$C_{ISS}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=-20\text{V}$ , $f=1\text{MHz}$		657		pF
$C_{OSS}$	Output Capacitance			143		pF
$C_{RSS}$	Reverse Transfer Capacitance			63		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		6.5		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$ , $V_{DS}=-20\text{V}$ , $I_D=-5\text{A}$		13.6		nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			6.8		nC
$Q_{gs}$	Gate Source Charge			1.8		nC
$Q_{gd}$	Gate Drain Charge			3.9		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$ , $V_{DS}=-20\text{V}$ , $R_L=4\Omega$ , $R_{GEN}=3\Omega$		7.5		ns
$t_r$	Turn-On Rise Time			6.7		ns
$t_{D(off)}$	Turn-Off DelayTime			26		ns
$t_f$	Turn-Off Fall Time			11.2		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		22.3		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		15.2		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $\leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

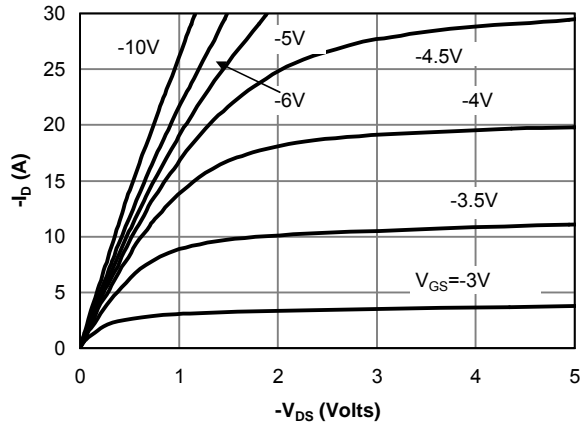


Fig 1: On-Region Characteristics

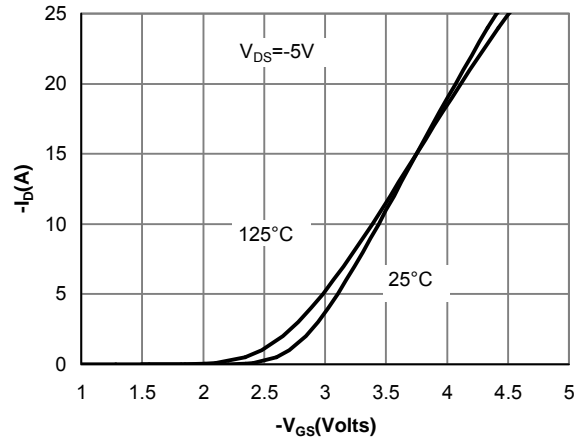


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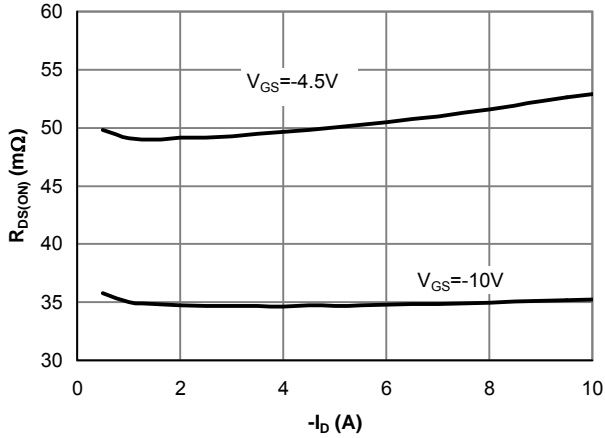


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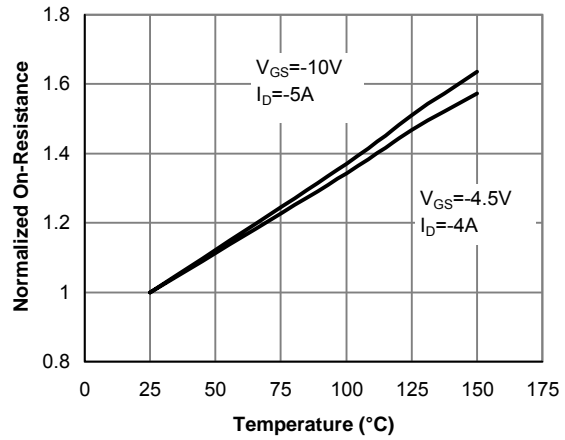


Figure 4: On-Resistance vs. Junction Temperature

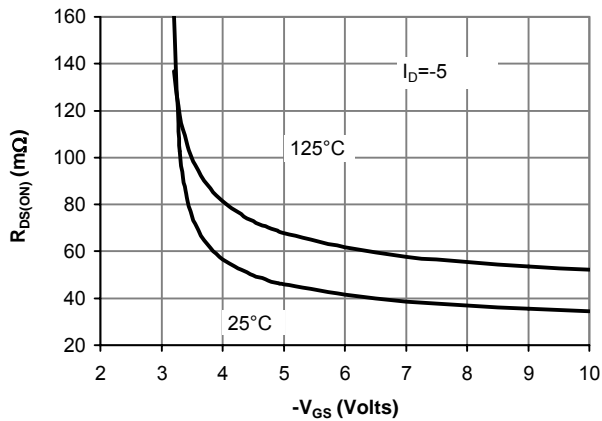


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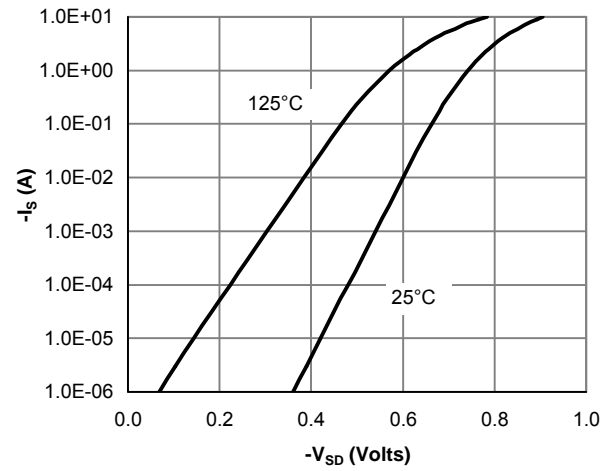


Figure 6: Body-Diode Characteristics

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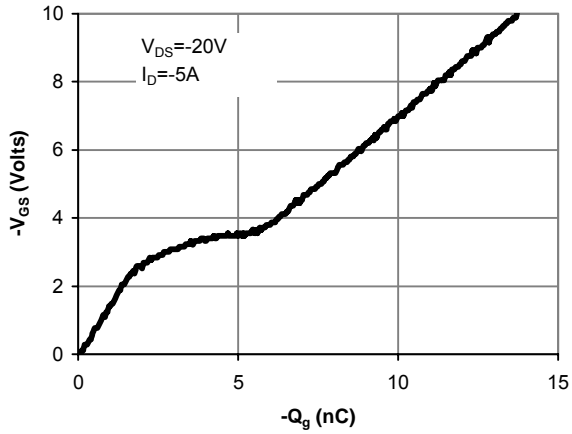


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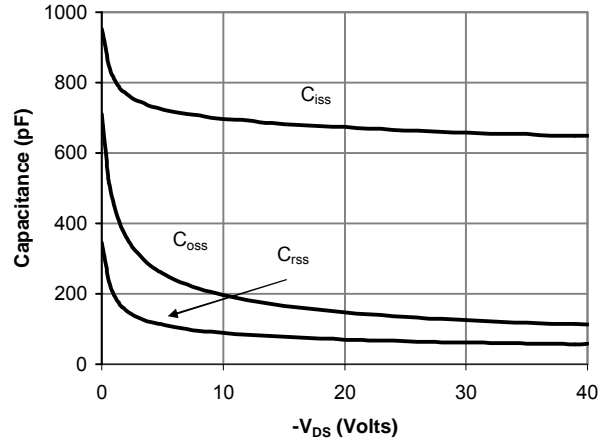


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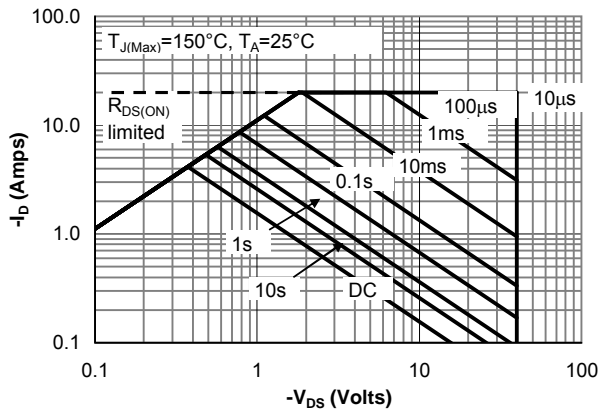


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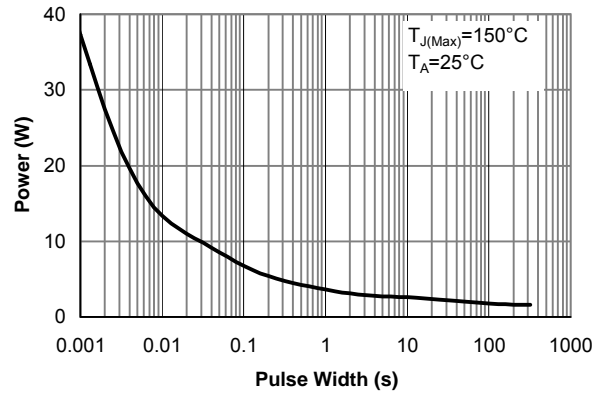


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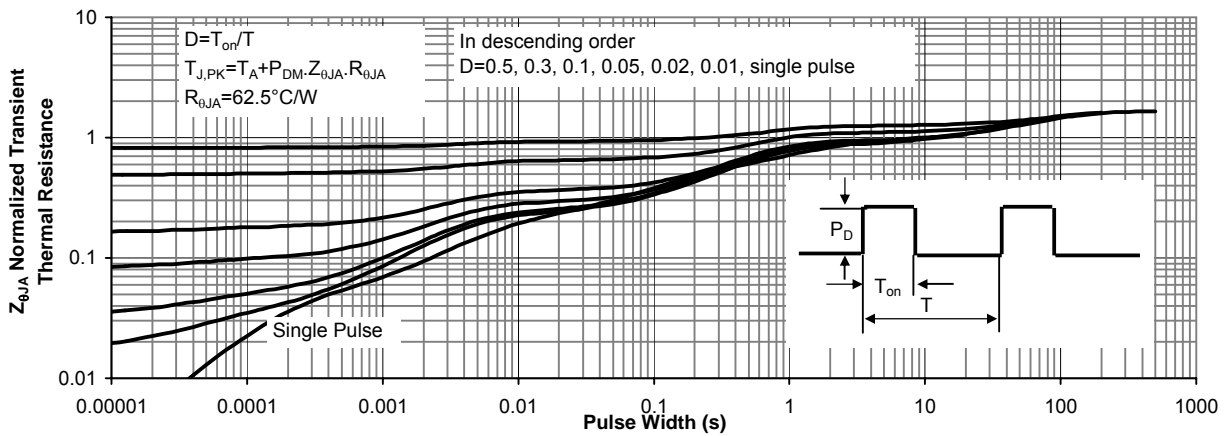


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